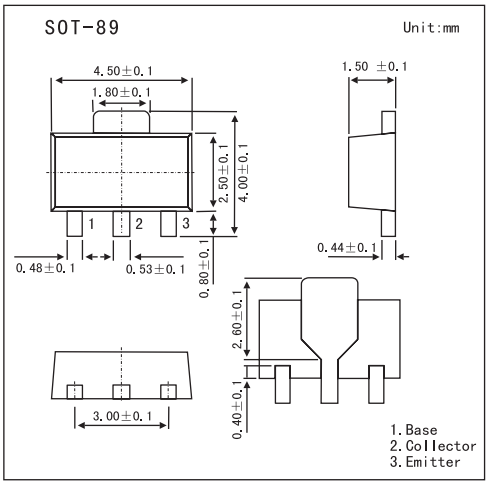
Power Transistor

2SB1260



■ Features

- High breakdown voltage and high current.BV_{CEO}= -80V, I_C=-1A
- Good hFE linearity.
- Low $V_{CE(sat)}$.
- Epitaxial planar type
- PNP silicon transistor

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Collector current(Pulse)	I_{CP} *	-2	A
Collector power dissipation	P_C	0.5	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Single pulse, Pw=100ms

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=-50μA	-80			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA	-80			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-50μA	-5			V
Collector cutoff current	I_{CBO}	V_{CB}=-60V			-1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-4V			-1	μA
Collector-emitter saturation voltage	h_{FE}	V_{CE}=-3V, I_C=-0.1A	82		390	
DC current transfer ratio	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA			-0.4	V
Transition frequency	Cob	V_{CE}=-5V, I_E=50mA, f=30MHz		100		MHz
Output capacitance	f_T	V_{CB}=-10V, I_E=0A, f=1MHz		25		pF

■ hFE Classification

Marking	BE		
Rank	P	Q	R
hFE	82～180	120～270	180～390